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# A molecular dynamics approach to simulate Raman and IR spectra of silicon nanowires

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### Introduction

- Raman/IR spectroscopy is one of the mayor methods to characterize nanostructures
- Raman spectra need to be interpreted  $\rightarrow$  input from theory needed
- Calculations of Raman spectra with density functional theory is straightforward for small systems
- Many nanostructures are much too big for these methods

**Task:** Simulate the Raman spectrum of nanostructures and interpret the spectrum in terms of phonon modes.







- 1. Model the geometry of the nanostructure
- Do a molecular dynamics simulation of the nanostructure
  → trajectories
- 3. Decompose the trajectories into phonon modes and filter out the
  - Raman active phonon modes
  - IR active phonon modes
- 4. Calculate the spectral function = Fourier transform of the **Velocity Autocorrelation Function**







#### 1. Geometry of a silicon nanowire









- 2. Molecular Dynamics Simulations
  - Density Functional Tight Binding (DFTB) method semi-empirical quantum mechanical method; fast; quite accurate for silicon
- 3. Decomposition of MD trajectories into phonon modes
  - use crystal symmetry analysis to find
    - all possible phonon displacements vectors (polarizations) at the  $\Gamma\text{-point}$
    - Raman/IR active modes

1 etc.:  $\vec{\epsilon}_j$ , j=1...3N

• Filter out a particular phonon from the MD trajectories by projection

$$v_j(t) = \vec{\epsilon}_j \cdot \vec{v}(t)$$







#### 4. Calculate the spectral function

- Spectral function ~ Fourier transform of the Velocity Autocorrelation Function = power spectrum of the phonon velocities
- Use the subset of Raman/IR active phonon velocities

$$P_{Raman}(\omega) = \sum_{j}^{j_{Raman}} \left| \int v_j(t) \exp(-i\omega t) \right|^2$$







### Results Raman spectra of Bulk Silicon: Temperature dependence



experiment



 $\rightarrow$  good agreement between experiment and theory:

• linear dependence + value for the slope







### Results Raman spectra of Si-nanowires with different diameters



- redshift of bulk peak
- frequency band with Gaussian shape at about 480 cm<sup>-1</sup>







### Results Raman spectra of Si-nanowires with different diameters



Wang et al., Phys. Rev. B **61**, 16827 (2000)

 $\rightarrow$  good agreement between experiment and theory







### Results Atom resolved Raman spectrum of a Si-nanowire









# Results Structural analysis of Si-nanowires



- surface layer has reduced bond lengths  $\rightarrow$  surface strain
- from the second layer on the system is like bulk silicon







### Summary

- Method to calculate Raman/IR spectra of nanostructures was developed
- Good agreement with experiment for
  - Temperature dependence of the Raman peak of bulk Si
  - Diameter dependence of the peak position/FWHM for the main Raman frequency band of Si nanowires
- Able to interpret the spectrum in terms of atomic displacements / phonon modes

#### THANK YOU FOR YOUR ATTENTION



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